3CG1

PNP Silicon High Frequency Low Power Transistor

Features:

1. Using epitaxy planar technology structure. High working frequency. Metallic packaging.
2. Small volume, light weight, easy installation.
3. Use for high frequency oscillation, high frequency small signal amplification, low power source adjustment circuit. Make up push pull amplifying circuit with NPN.
4. Quality Class: GS, G. Implementation of standards: QZJ840611

TECHNICAL DATA: **(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications							Test Condition
			A	B	C	D	E	F	G	
Total Dissipation	P_{tot}	mW	300							Ta=25°C
Max. Collector Current	I_{CM}	mA	30							
Junction Temperature	T_{jm}	°C	175							
Storage Temperature	T_{stg}	°C	-55~+175							
C-E Breakdown Voltage	$V_{(BR)CEO}$	V	15	20	30	40	50	60	70	I_C=0.1mA
E-B Breakdown Voltage	$V_{(BR)EBO}$	V	4							I_E=0.1mA
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	0.5							I_C=30mA, I_B=3mA
C-E Leakage Current	I_{CEO}	uA	1.0							V_{CE}=10V
DC Current Gain	h_{FE}		25~~270							V_{CE}=10V, I_C=10mA
Transition frequency	f_T	MHz	150							V_{CE}=10V, I_C=10mA f=30MHz

h_{FE} Colored:

Color	Orange	Yellow	Green	Blue	Purple	Gray
h_{FE}	25~40	40~55	55~80	80~120	120~180	180~270

Outline and Dimensions: